

# **MSN4902**

## **Preliminary Datasheet**

## N-Channel 60-V (D-S) MOSFET

#### FEATURES

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application
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Portable Devices

Consumer Electronics

#### Mechanical

●Case: SOP-8-Dual Package

#### **Packing Information**

Package	Packing
SOP-8-Dual	3K/13" Reel

Maximum Ratings (T <sub>A</sub> =25°C unless otherwise specified)					
Parameter	Symbol	Limit	Unit		
DrainSource Voltage	V <sub>DS</sub>	60	V		
GateSource Voltage	V <sub>GS</sub>	±20	V		
Continuous Drain Current <sup>4)</sup>	Ι <sub>D</sub>	5	А		
Maximum Power Dissipation	P <sub>D</sub>	1.2	W		
Pulsed Drain Current <sup>1)</sup>	I <sub>DM</sub>	20	А		
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	55~150	°C		

Typical Thermal Resistance			
Parameter	Symbol	Limit	Unit
JunctiontoAmbient Thermal Resistance	$R_{ extsf{ heta}JA}$	62.5	°C/W

NOTES :

1. Pulse width<300us, Duty cycle<2%.

2. Essentially independent of operating temperature typical characteristics.

3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.

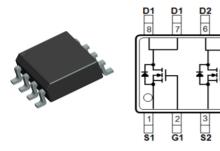
4. The maximum current rating is package limited.

5. RQJA is the sum of the junctiontocase and casetoambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain nins. Mounted on a 1 inch2 with 2oz square rad of conner

pins. Mounted on a 1 inch2 with 2oz.square pad of copper. 6. Guaranteed by design, not subject to production testing.

PRODUCTY SUMMARY				
$V_{\rm DS}$	R	<sub>DS(on)</sub> m(Ω)	I <sub>D</sub> (A)	
60	46	Rdson @-10V	4.8	
60	54	Rdson @-4.5V	4.5	

## SOP-8-Dual





Electrical C	haracteristi	<b>CS (T<sub>A</sub> = 25°C UNLESS OTH</b>	ERWISE	NOTED)		
Characteristics	Symbol	Test Condition	Limits			11
Characteristics			Min	Тур	Max	Unit
		Static				
DrainSource Breakdown Voltage	B <sub>VDSS</sub>	$V_{GS} = 0V, I_{D} = 250uA$	60	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	1.00	1.60	3.00	V
DrainSource OnState Resistance	R	$V_{GS}$ =10V, $I_{D}$ =4.8A	-	40	46	mΩ
	$R_{DS(on)}$	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.5A	-	46	54	mΩ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =60V, $V_{GS}$ =0V			1	uA
GateSource Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V			±100	nA
	1	Dynamic <sup>3)</sup>				
Total Gate Charge	Q <sub>g</sub>		-	16	-	nC
GateSource Charge	Q <sub>gs</sub>	VDS = 30 V, VGS = 4.5 V, ID = 5.4 A	-	3.9	-	nC
GateDrain Charge	Q <sub>gd</sub>		-	8.2	-	nC
Input Capacitance	C <sub>iss</sub>		-	1460	-	pF
Output Capacitance	C <sub>oss</sub>	VDS = 15 V, VGS = 0 V, f = 1 MHz	-	125	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	110	-	pF
	•	•				
		Switching				
TurnOn Delay Time	t <sub>d(on)</sub>		-	8	-	ns
TurnOn Rise Time	t <sub>r</sub>	VDS = 30 V, RL = 5.6	-	9	-	ns
TurnOff Delay Time	t <sub>d(off)</sub>	Ω, ID = 5.4 A, VGEN = 10 V, RGEN = 6 Ω	-	49	-	ns
TurnOff Fall Time	t <sub>f</sub>		-	14	-	ns
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	Dr	ainSource Diode				
Maximum Continuous Body Diode	I <sub>S</sub>	VG=VD=0V , Force Current	-	-	1.2	А
Diode Forward Voltage	V <sub>SD</sub>	IS=1.0A, VGS=0V	-	-	1.5	V

Note:

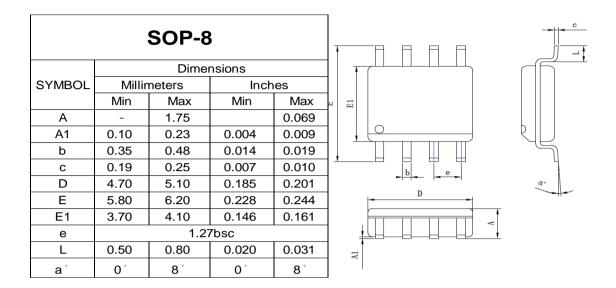
1. Pulse width<300us, Duty cycle<2%

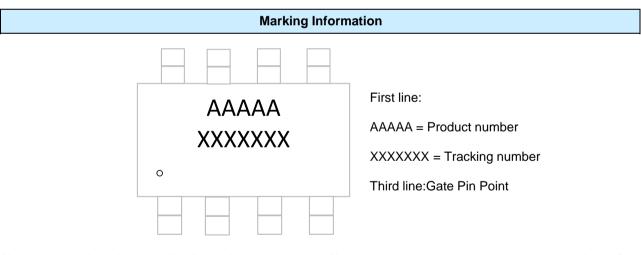
2. Fused current that based on wire numbers and diameter

3. Guaranteed by design, not subject to production testing.



Package Outline Dimensions (inches and millimeters)





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